

In the Claims

Please add new claims 38-49 in accordance with 37 C.F.R. § 1.121(c)(1)(i). A marked up version showing amendments is not required.

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38.<sup>13</sup> (new) A capacitor construction comprising a first capacitor electrode over a substrate, a capacitor dielectric layer over the first electrode, a second capacitor electrode over the dielectric layer, and an atomic layer deposited metal-containing conductive layer between the first and second electrodes.

39.<sup>14</sup> (new) The construction of claim ~~38~~<sup>13</sup> wherein the atomic layer deposited conductive layer is on the first electrode.

40.<sup>15</sup> (new) The construction of claim ~~38~~<sup>13</sup> wherein the atomic layer deposited conductive layer comprises elemental metal, a metal alloy, or a metal-containing compound.

41.<sup>16</sup> (new) The construction of claim ~~38~~<sup>13</sup> wherein the atomic layer deposited conductive layer comprises WN, WSiN, TaN, TiN, TiSiN, Pt, Pt alloys, Ir, Ir alloys, Pd, Pd alloys, RuO<sub>x</sub>, or IrO<sub>x</sub>.

42.<sup>17</sup> (new) The construction of claim ~~38~~<sup>13</sup> wherein at least one of the first or second electrode comprises polysilicon and the dielectric layer comprises oxygen.

- 43.<sup>18</sup> A capacitor construction comprising:
- a first capacitor electrode over a substrate;
  - a metal-containing conductive material over the first electrode, the material comprising a chemisorption product of first and second precursor layers;
  - a capacitor dielectric layer over the first electrode; and
  - a second capacitor electrode over the dielectric layer.

- 44.<sup>19</sup> (new) The construction of claim 43<sup>18</sup> wherein the first and second precursor layers each consist essentially of a monolayer.

- 45.<sup>20</sup> (new) The construction of claim 43<sup>18</sup> wherein the first and second precursors respectively comprise only one of the following pairs:  $\text{WF}_6/\text{NH}_3$ ,  $\text{TaCl}_5/\text{NH}_3$ ,  $\text{TiCl}_4/\text{NH}_3$ , tetrakis(dimethylamido)titanium/ $\text{NH}_3$ , ruthenium cyclopentadiene/ $\text{H}_2\text{O}$ ,  $\text{IrF}_5/\text{H}_2\text{O}$ , organometallic  $\text{Pt}/\text{H}_2\text{O}$ .

- 46.<sup>21</sup> (new) The construction of claim 43<sup>18</sup> wherein the atomic layer deposited conductive material is on the first electrode.

- 47.<sup>22</sup> (new) The construction of claim 43<sup>18</sup> wherein the atomic layer deposited conductive material comprises elemental metal, a metal alloy, or a metal containing compound

- 48.<sup>23</sup> (new) The construction of claim 43<sup>18</sup> wherein the conductive material comprises  $\text{WN}$ ,  $\text{WSiN}$ ,  $\text{TaN}$ ,  $\text{TiN}$ ,  $\text{TiSiN}$ ,  $\text{Pt}$ ,  $\text{Pt}$  alloys,  $\text{Ir}$ ,  $\text{Ir}$  alloys,  $\text{Pd}$ ,  $\text{Pd}$  alloys,  $\text{RuO}_x$ , or  $\text{IrO}_x$ .

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49. <sup>24</sup> (new) The construction of claim <sup>18</sup> 43 wherein at least one of the first or second electrode comprises polysilicon and the dielectric layer comprises oxygen.